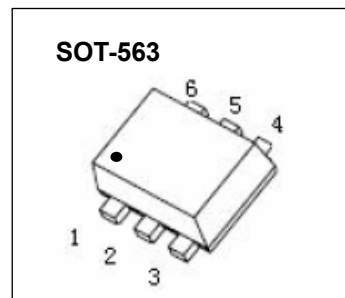


Plastic-Encapsulate MOSFETS

N Channel +P Channel MOSFET

$V_{(BR)DSS}$	$R_{DS(on)MAX}$	I_D
20V	380mΩ@4.5V	0.75A
	450mΩ@2.5V	
	800mΩ@1.8V	
-20V	520mΩ@-4.5V	-0.66A
	700mΩ@-2.5V	
	950mΩ(TYP)@-1.8V	



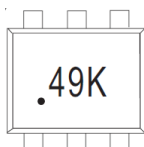
FEATURE

- Surface Mount Package
- Low $R_{DS(on)}$
- Operated at Low Logic Level Gate Drive
- ESD Protected Gate
- Including a N-ch CJ3134K and a P-ch CJ3139K (independently) In a Package

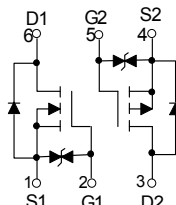
APPLICATION

- Load/ Power Switching
- Interfacing Switching
- Battery Management for Ultra Small Portable Electronics
- Logic Level Shift

MARKING



Equivalent Circuit



ABSOLUTE MAXIMUM RATINGS ($T_a=25^\circ\text{C}$ unless otherwise noted)

Parameter	Symbol	Value	Unit
N-MOSFET			
Drain-Source Voltage	V_{DS}	20	V
Typical Gate-Source Voltage	V_{GS}	±12	V
Continuous Drain Current (note 1)	I_D	0.75	A
Pulsed Drain Current ($t_p=10\mu\text{s}$)	I_{DM}	1.8	A
P-MOSFET			
Drain-Source Voltage	V_{DS}	-20	V
Typical Gate-Source Voltage	V_{GS}	±12	V
Continuous Drain Current (note 1)	I_D	-0.66	A
Pulsed Drain Current ($t_p=10\mu\text{s}$)	I_{DM}	-1.2	A
Temperature and Thermal Resistance			
Thermal Resistance from Junction to Ambient (note 1)	$R_{\theta JA}$	833	$^\circ\text{C/W}$
Junction Temperature	T_J	150	$^\circ\text{C}$
Storage Temperature	T_{STG}	-55~+150	$^\circ\text{C}$
Lead Temperature for Soldering Purposes(1/8" from case for 10 s)	T_L	260	$^\circ\text{C}$

MOSFET ELECTRICAL CHARACTERISTICS

N-ch MOSFET ELECTRICAL CHARACTERISTICS($T_a=25^{\circ}\text{C}$ unless otherwise noted)

Parameter	Symbol	Test Condition	Min	Typ	Max	Unit
STATIC CHARACTERISTICS						
Drain-source breakdown voltage	V _{(BR)DSS}	V _{GS} = 0V, I _D =250μA	20			V
Zero gate voltage drain current	I _{DSS}	V _{DS} =20V, V _{GS} = 0V			1	μA
Gate-body leakage current	I _{GSS}	V _{GS} =±10V, V _{DS} = 0V			±20	uA
Gate threshold voltage (note 2)	V _{GS(th)}	V _{DS} =V _{GS} , I _D =250μA	0.35		1.1	V
Drain-source on-resistance(note 2)	R _{DS(on)}	V _{GS} =4.5V, I _D =0.65A		180	380	mΩ
		V _{GS} =2.5V, I _D =0.55A		270	450	mΩ
		V _{GS} =1.8V, I _D =0.45A		600	800	mΩ
Forward tranconductance(note 2)	g _{FS}	V _{DS} =10V, I _D =0.8A		1.6		S
Diode forward voltage	V _{SD}	I _S =0.15A, V _{GS} = 0V			1.2	V
DYNAMIC CHARACTERISTICS (note 4)						
Input Capacitance	C _{iss}	V _{DS} =16V, V _{GS} =0V, f =1MHz		79	120	pF
Output Capacitance	C _{oss}			13	20	pF
Reverse Transfer Capacitance	C _{rss}			9	15	pF
SWITCHING CHARACTERISTICS (note 3,4)						
Turn-on delay time	t _{d(on)}	V _{GS} =4.5V, V _{DS} =10V, I _D =500mA, R _{GEN} =10Ω		6.7		ns
Turn-on rise time	t _r			4.8		ns
Turn-off delay time	t _{d(off)}			17.3		ns
Turn-off fall time	t _f			7.4		ns

P-ch MOSFET ELECTRICAL CHARACTERISTICS($T_a=25^{\circ}\text{C}$ unless otherwise noted)

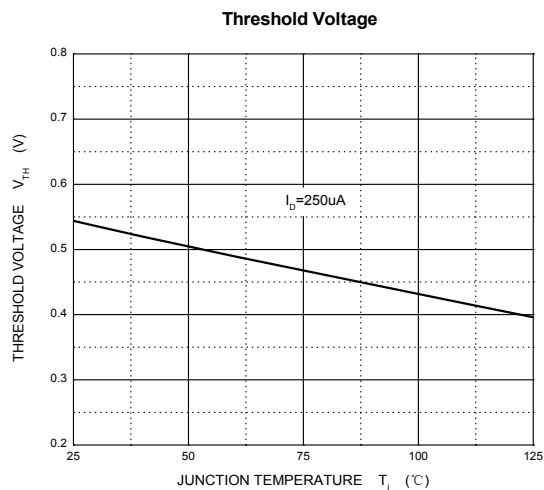
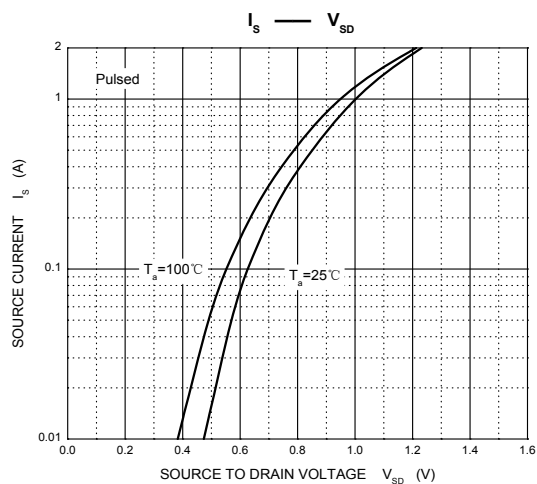
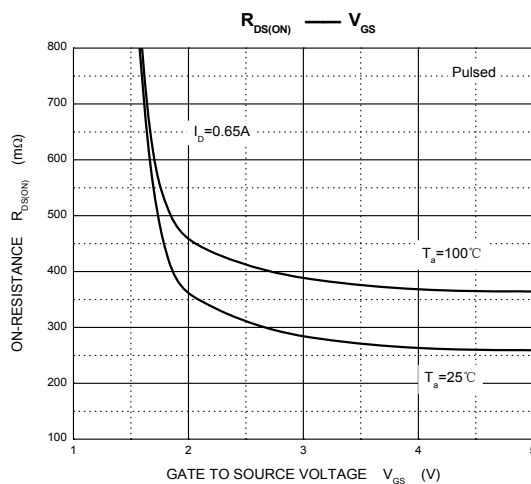
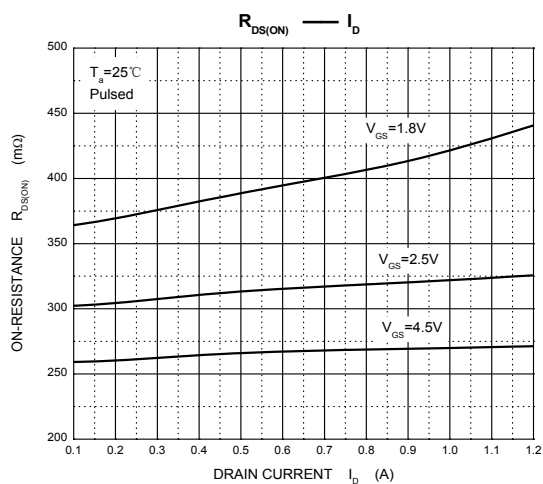
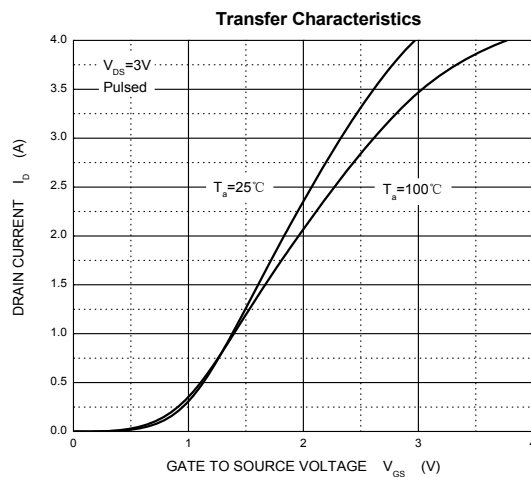
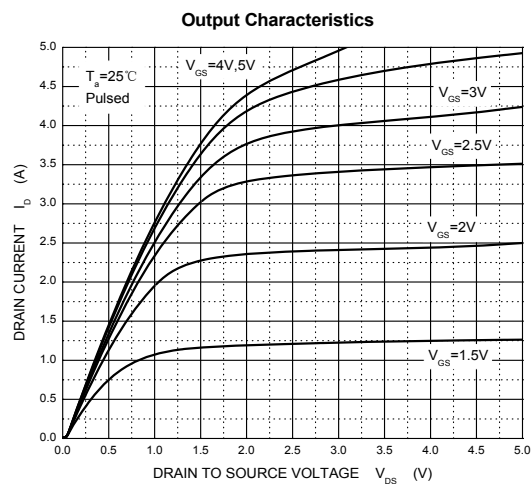
Parameter	Symbol	Test Condition	Min	Typ	Max	Unit
STATIC CHARACTERISTICS						
Drain-source breakdown voltage	$V_{(BR)DSS}$	$V_{GS} = 0V, I_D = -250\mu A$	-20			V
Zero gate voltage drain current	I_{DSS}	$V_{DS} = -20V, V_{GS} = 0V$			-1	μA
Gate-body leakage current	I_{GSS}	$V_{GS} = \pm 10V, V_{DS} = 0V$			± 20	μA
Gate threshold voltage (note 2)	$V_{GS(th)}$	$V_{DS} = V_{GS}, I_D = -250\mu A$	-0.35		-1.1	V
Drain-source on-resistance(note 2)	$R_{DS(on)}$	$V_{GS} = -4.5V, I_D = -1A$		320	520	m Ω
		$V_{GS} = -2.5V, I_D = -0.8A$		440	700	m Ω
		$V_{GS} = -1.8V, I_D = -0.5A$		650		m Ω
Forward tranconductance(note 2)	g_{FS}	$V_{DS} = -10V, I_D = -0.54A$		1.2		S
Diode forward voltage	V_{SD}	$I_S = -0.5A, V_{GS} = 0V$			-1.2	V
DYNAMIC CHARACTERISTICS (note 4)						
Input Capacitance	C_{iss}	$V_{DS} = -16V, V_{GS} = 0V, f = 1MHz$		113	170	pF
Output Capacitance	C_{oss}			15	25	pF
Reverse Transfer Capacitance	C_{rss}			9	15	pF
SWITCHING CHARACTERISTICS (note 3,4)						
Turn-on delay time	$t_{d(on)}$	$V_{GS} = -4.5V, V_{DS} = -10V, I_D = -200mA, R_{GEN} = 10\Omega$		9		ns
Turn-on rise time	t_r			5.8		ns
Turn-off delay time	$t_{d(off)}$			32.7		ns
Turn-off fall time	t_f			20.3		ns

Notes :

- 1.Surface mounted on FR4 board using the minimum recommended pad size.
2. Pulse Test : Pulse width=300 μs , duty cycles $\leq 2\%$.
3. Switching characteristics are independent of operating junction temperature.
4. Garanted by design, not subject to producing.

Typical Characteristics

N-Channel MOS



Typical Characteristics

P-Channel MOS

